

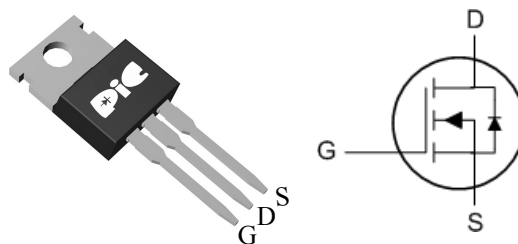
➤ General Description

This PAN80TG24AG N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology
- TO-220 package design

➤ TO-220



➤ Application

- SMPS Power Supplier.
- Charger Adapter
- Power Tools
- LED Lighting

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_C=25^\circ C$	108	A
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_C=100^\circ C$	68	A
Pulsed Drain Current ²	I_{DM}	200	A
Single Pulse Avalanche Energy ³	EAS	125	mJ
Avalanche Current	I_{AS}	50	A
Total Power Dissipation ⁴	$P_D @ T_C=25^\circ C$	149	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ C$
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	55	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	0.84	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$, $I_D=250\mu A$	80	---	---	V
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	$V_{GS}=10V$, $I_D=30A$	---	---	6.5	$m\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=64V$, $V_{GS}=0V$, $T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=64V$, $V_{GS}=0V$, $T_J=55^\circ C$	---	---	5	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=5V$, $I_D=30A$	---	50	---	S
Gate Resistance	R_g	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	1.4	---	Ω
Total Gate Charge (10V)	Q_g	$V_{DS}=64V$, $V_{GS}=10V$, $I_D=30A$	---	83.7	---	nC
Gate-Source Charge	Q_{gs}		---	28.6	---	
Gate-Drain Charge	Q_{gd}		---	29.3	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=40V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=30A$	---	38.1	---	ns
Rise Time	T_r		---	73.3	---	
Turn-Off Delay Time	$T_{d(off)}$		---	51.6	---	
Fall Time	T_f		---	26.1	---	
Input Capacitance	C_{iss}	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	5580	---	pF
Output Capacitance	C_{oss}		---	571	---	
Reverse Transfer Capacitance	C_{rss}		---	278	---	

➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5}	I_S	$V_G=V_D=0V$, Force Current	---	---	70	A
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V$, $I_S=A$, $T_J=25^\circ C$	---	---	1.2	V
Reverse Recovery Time	t_{rr}	$I_F=30A$, $dI/dt=100A/\mu s$,	---	26.7	---	nS
Reverse Recovery Charge	Q_{rr}	$T_J=25^\circ C$	---	27.9	---	nC

Note :

1.Pulse width limited by maximum junction temperature.

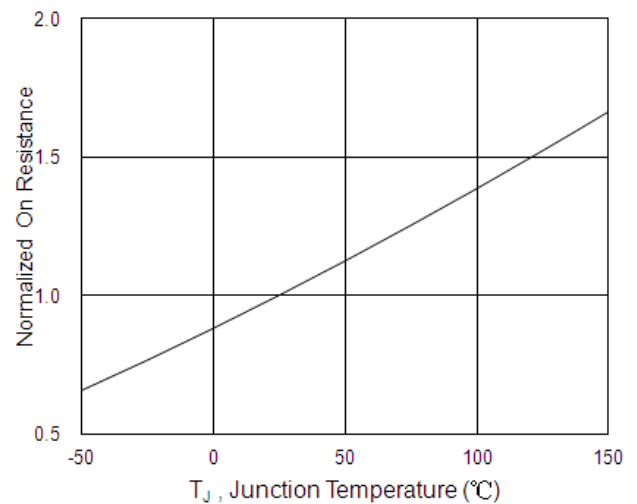
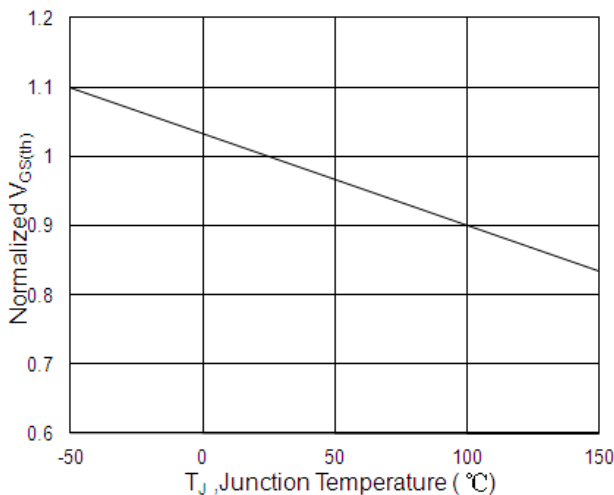
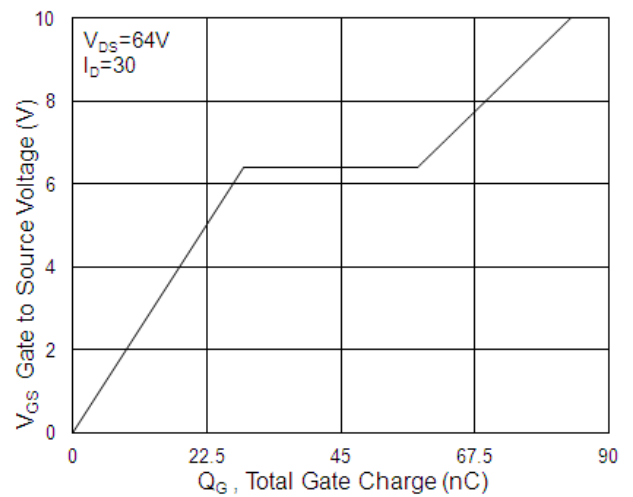
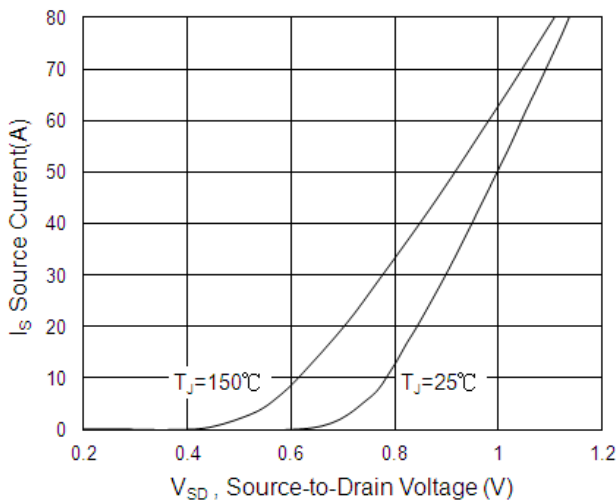
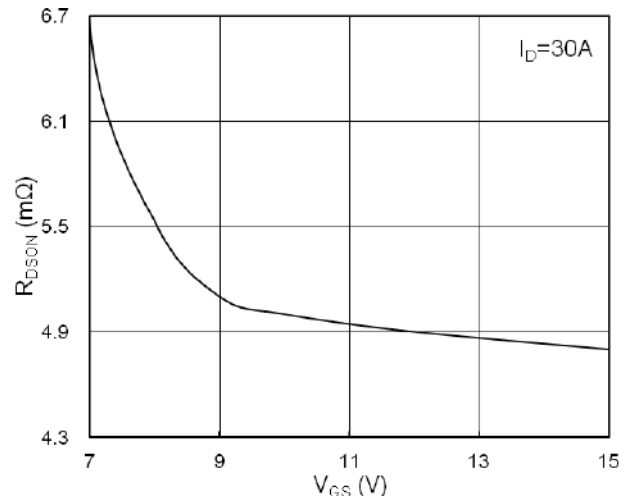
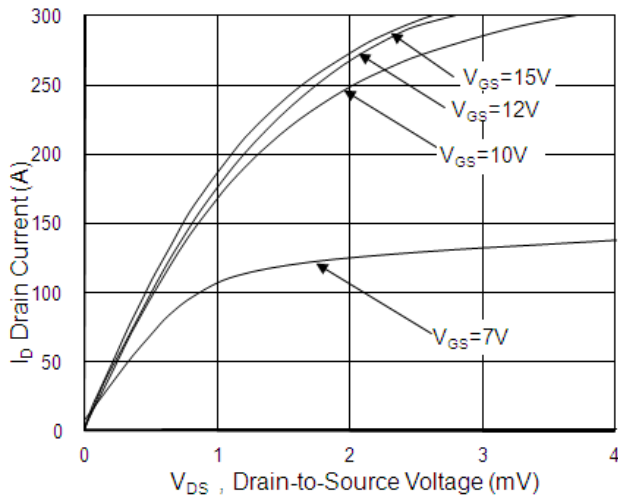
2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=50A$

4.Ensure that the channel temperature does not exceed $150^\circ C$.

5.The data is theoretically the same as I_D and IDM , in real applications , should be limited by total power dissipation.

➤ Typical Characteristics



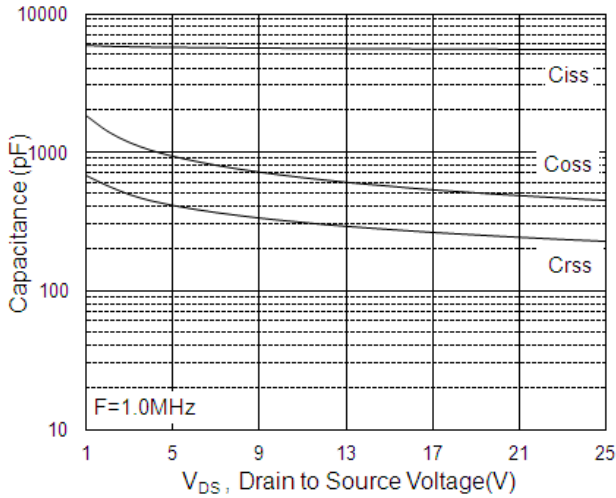


Fig.7 Capacitance

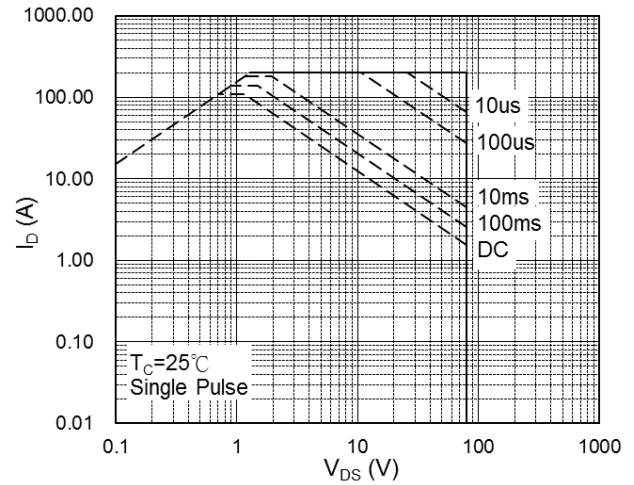


Fig.8 Safe Operating Area

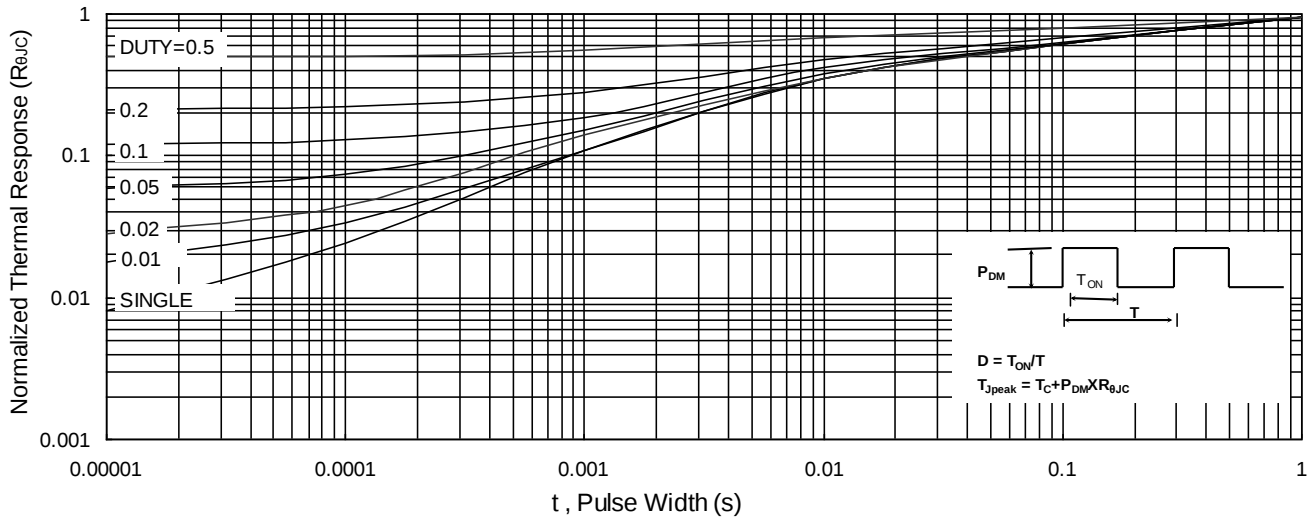


Fig.9 Normalized Maximum Transient Thermal Impedance

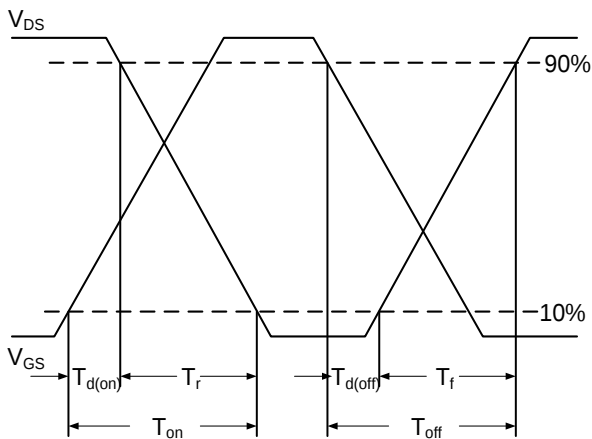


Fig.10 Switching Time Waveform

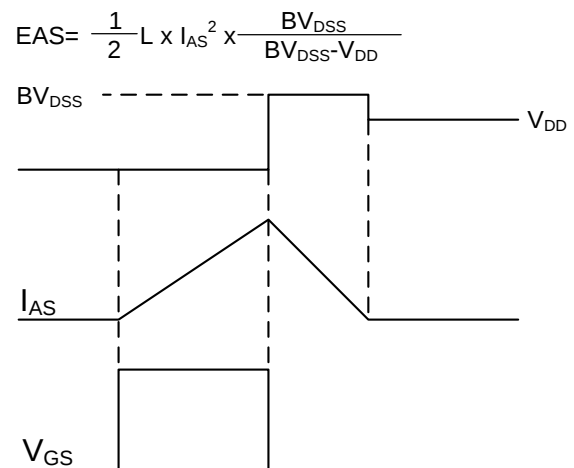


Fig.11 Unclamped Inductive Switching Waveform

➤ Recommend IR Reflow Soldering Thermal Profile



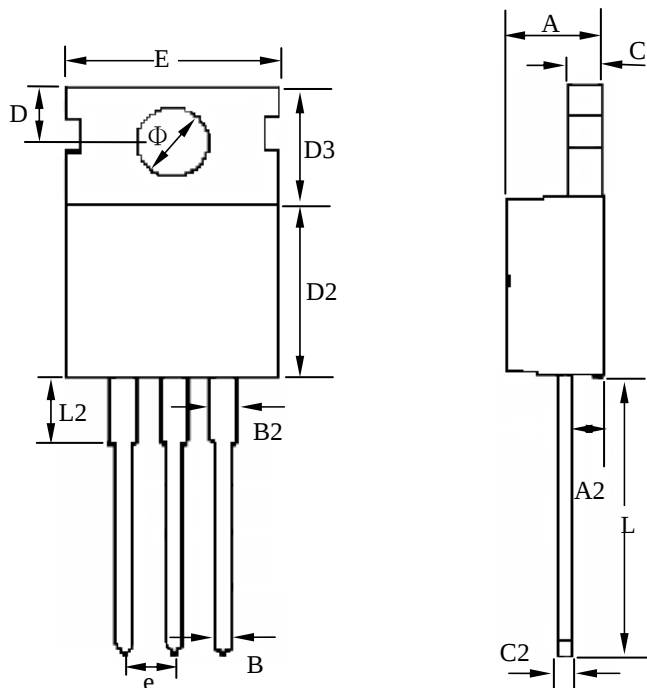
Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	150°C
Temperature Max. (T_{smax})	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN80TG24AG	TO-220	50 pcs/tube

N-Ch 80V Fast Switching MOSFET
 $V_{DS}=80V$, $I_D=108A$, $R_{DS(ON)}=6.5m\Omega$

➤ Package Information (TO-220)



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.25	--	4.80	0.167	--	0.189
A2	2.20	--	2.92	0.087	--	0.115
B	0.70	--	0.91	0.028	--	0.036
B2	1.15	--	1.77	0.045	--	0.070
C	1.20	--	1.40	0.047	--	0.055
C2	0.45	--	0.61	0.018	--	0.024
D	2.54	--	3.00	0.100	--	0.118
D2	8.39	--	9.47	0.330	--	0.373
D3	6.30	--	6.70	0.248	--	0.264
E	9.70	--	10.36	0.382	--	0.408
L	12.75	--	14.40	0.502	--	0.567
L2	2.45	--	4.05	0.096	--	0.159
Φ	3.50	--	3.80	0.138	--	0.150
e	--	2.54	--	--	0.100	--

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